WEST Search History



DATE: Monday, December 05, 2005

Hide?	Set Name	Query	Hit Count
	DB=PGPB	R,USPT,EPAB,JPAB,DWPI; THES=ASSIGNEE; PLUR=YI	ES; OP=ADJ
	L1	host.clm. and dopant.clm. and powder.clm.	31
	L2	L1 and melt\$4.clm.	4
	L3	host same dopant same melt\$4 same container	5

END OF SEARCH HISTORY

WEST Search History

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DATE: Monday, December 05, 2005

Hide?	Set Name	Query	Hit Count
	DB=PGPE	R,USPT,EPAB,JPAB,DWPI; THES=ASSIGNEE; PLUR=YE	S; OP=ADJ
	L1	host.clm. and dopant.clm. and powder.clm.	31
	L2	L1 and melt\$4.clm.	4
	L3	host same dopant same melt\$4 same container	5
	L4	5242531.pn.	2

END OF SEARCH HISTORY

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L3: Entry 3 of 5

File: USPT

Jul 3, 2001

DOCUMENT-IDENTIFIER: US 6254674 B1

TITLE: Method of controllably delivering dopant by limiting the release rate of

dopant from a submerged vessel

Brief Summary Text (8):

U.S. Pat. No. 5,242,531 to Klingshirn et al. discloses a process for continuously recharging a <u>melt</u> crucible with additional molten <u>host</u> material and additional molten <u>dopant</u>. In this regard, the Klingshirn '531 et al. patent describes separate <u>containers</u> filled with the <u>host</u> material and the <u>dopant</u> that are positioned above the <u>melt</u> crucible. Feedlines connect the <u>containers</u> with an additional crucible or <u>container in which the host</u> material and the <u>dopant</u> are mixed and <u>melted</u>. This additional crucible includes an outlet for supplying additional molten semiconductor material to the <u>melt</u> in order to recharge the <u>melt</u> during the crystal-growing process. While the '531 Klingshirn et al. patent addresses some of the issues with respect to controlling the amount of <u>dopant in the melt</u> throughout the course of a crystal-growing process, the technique described by the '531 Kingshirn et al. patent requires multiple <u>containers</u> positioned above the <u>melt</u> crucible which may complicate the design of the crystal-growing furnace and limit access to the melt crucible during the crystal-growing process.

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L3: Entry 4 of 5

File: USPT

Jan 30, 2001

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DOCUMENT-IDENTIFIER: US 6179914 B1

TITLE: Dopant delivery system and method

Brief Summary Text (8):

U.S. Pat. No. 5,242,531 to Klingshirn et al. discloses a process for continuously recharging a <u>melt</u> crucible with additional molten <u>host</u> material and additional molten <u>dopant</u>. In this regard, the Klingshirn '531 et al. patent describes separate <u>containers</u> filled with the <u>host</u> material and the <u>dopant</u> that are positioned above the <u>melt</u> crucible. Feedlines connect the <u>containers</u> with an additional crucible or <u>container in which the host</u> material and the <u>dopant</u> are mixed and <u>melted</u>. This additional crucible includes an outlet for supplying additional molten semiconductor material to the <u>melt</u> in order to recharge the <u>melt</u> during the crystal-growing process. While the '531 Klingshirn et al. patent addresses some of the issues with respect to controlling the amount of <u>dopant in the melt</u> throughout the course of a crystal-growing process, the technique described by the '531 Kingshirn et al. patent requires multiple <u>containers</u> positioned above the <u>melt</u> crucible which may complicate the design of the crystal-growing furnace and limit access to the melt crucible during the crystal-growing process.

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WEST Search History



DATE: Friday, December 02, 2005

Hide	? Set Nam	e Query	Hit Count
	DB=PG	PB, USPT, EPAB, JPAB, DWPI; THES=ASSIGNEE; PLUR=YES	; OP=ADJ
	L1	264/112.ccls. and 264/308.ccls.	8
	L2	264/113.ccls. and 264/308.ccls.	38
	L3	264/113.ccls. and 264/401.ccls.	17
	L4	264/112.ccls. and 264/401.ccls.	2
	L5	L1 and binder.clm.	3
	L6	L2 and binder.clm.	13
	L7	L3 and binder.clm.	5
	L8	L4 and binder.clm.	1
Ļ	L9	6733528.pn. and activation agent	0
	L10	6403002.pn. and activation agent	0
	L11	6322728.pn. and activation agent	0
	L12	6322728.pn. and (acid or amine or alcohol or ketone or salt)	1
	L13	6733528.pn. and (acid or amine or alcohol or ketone or salt)	1
	L14	6403002.pn. and (acid or amine or alcohol or ketone or salt)	1
	L15	hochsmann.IN. and activation agent	2
	L16	ederer.IN. and activation agent	3
	L17	ghosh.IN. host.clm. and dopant.clm.	0
	L18	ghosh.IN. and host.clm. and dopant.clm.	12
	L19	carlton.IN. and host.clm. and dopant.clm.	14
<u>ا</u>	L20	hatwar.IN. and host.clm. and dopant.clm.	31
	L21	L20 and seal\$4.clm.	2
	L22	L19 and seal\$4.clm.	2
	L23	L18 and seal\$4.clm.	2

END OF SEARCH HISTORY